

**HIGH ISOLATION VOLTAGE
STANDARD MULTI PHOTOCOUPLER SERIES
SINGLE TRANSISTOR TYPE**

-NEPOC™ Series-

DESCRIPTION

The PS2511-1, -2, -4 and PS2511L-1, -2, -4 are optically coupled isolators containing a GaAs light emitting diode and an NPN silicon phototransistor.

The PS2511-1, -2, -4 are in a plastic DIP (Dual In-line Package) and the PS2511L-1, -2, -4 are lead bending type (Gull-wing) for surface mount.

FEATURES

- High isolation voltage (BV = 5 000 Vr.m.s.)
- High current transfer ratio (CTR = 200 % TYP.)
- High-speed switching ($t_r = 3 \mu s$ TYP., $t_f = 5 \mu s$ TYP.)
- Taping Product number : PS2511L-1-E3, E4, F3, F4, PS2511L-2-E3, E4
- UL approved : File No. E72422 (S)

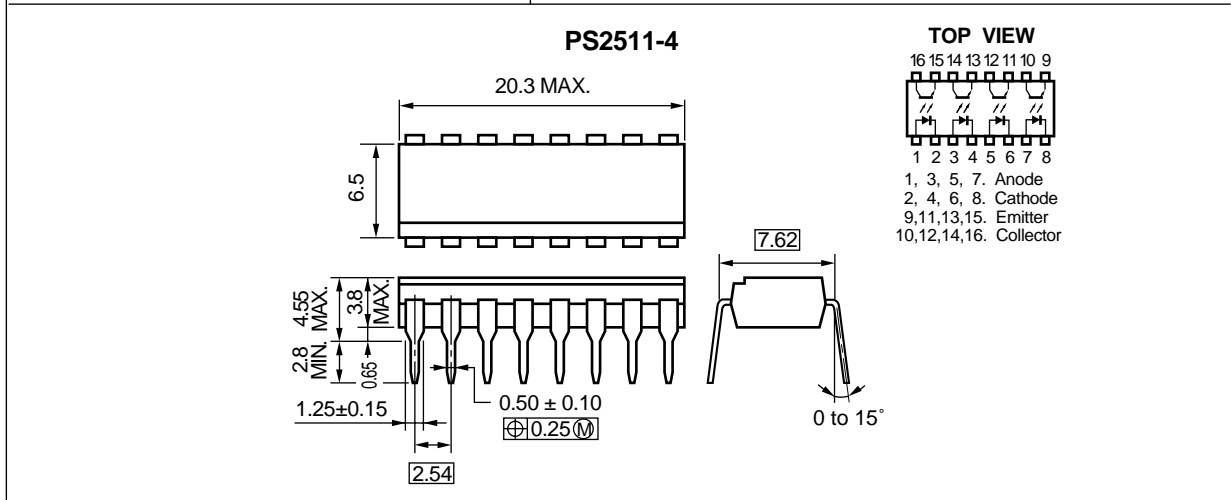
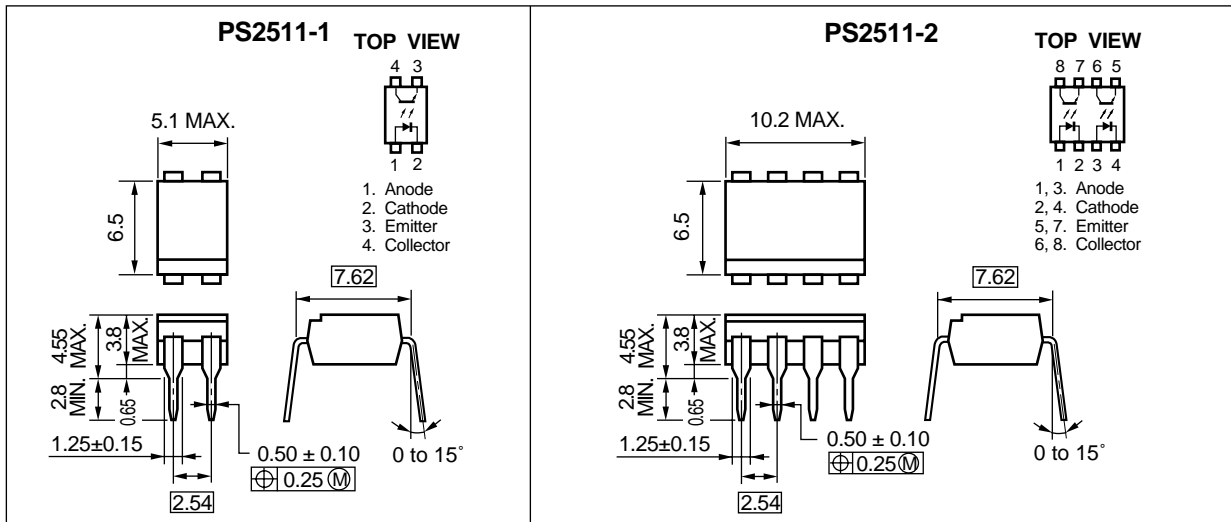
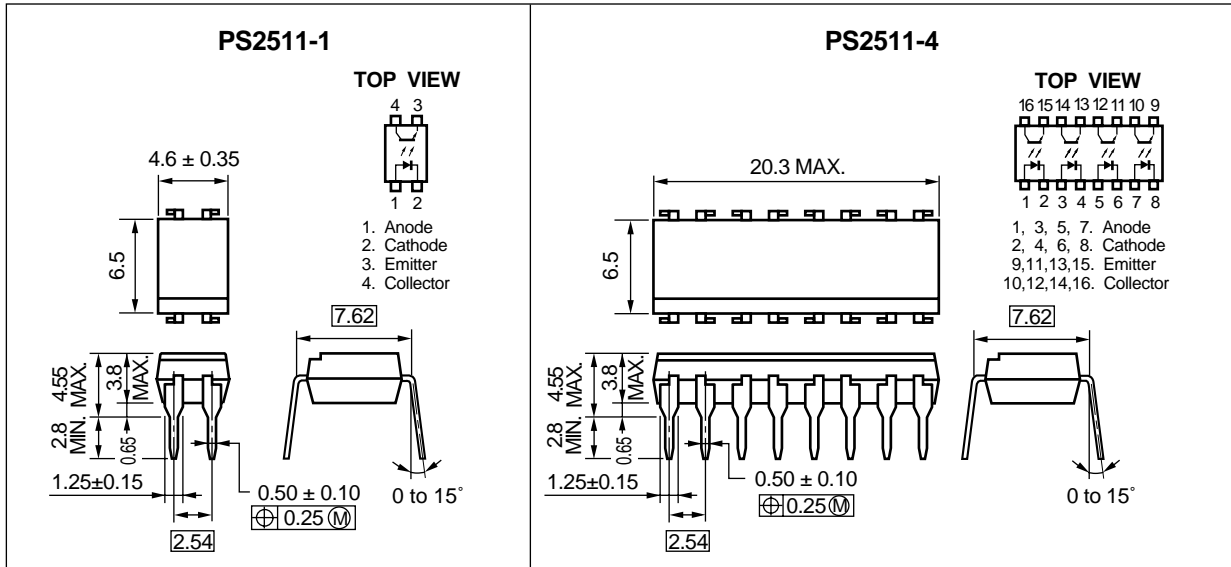
APPLICATIONS

- Power supply
- Telephone/FAX.
- FA/OA equipment
- Programmable logic controller

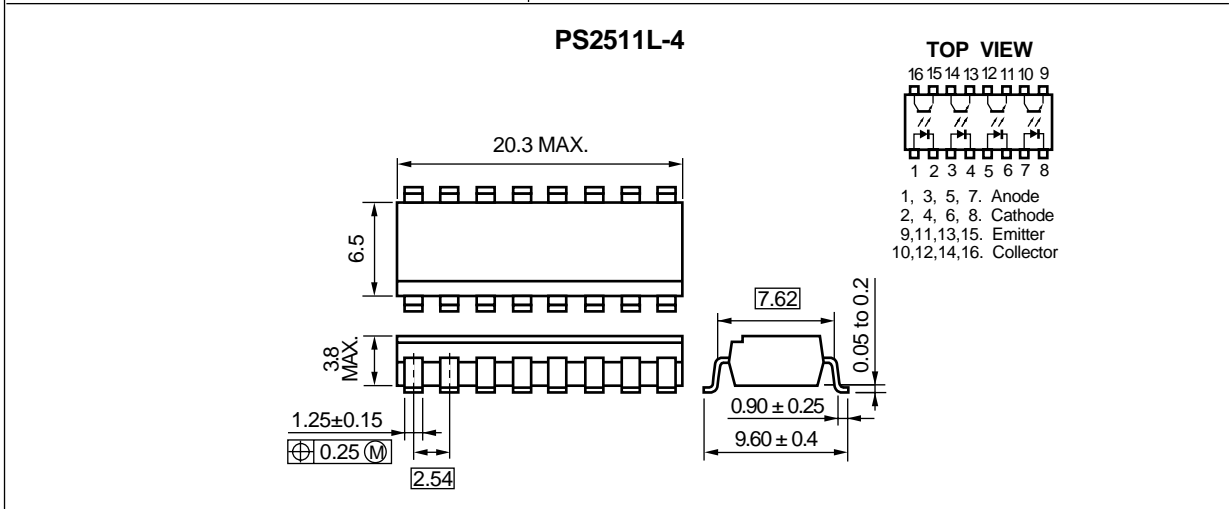
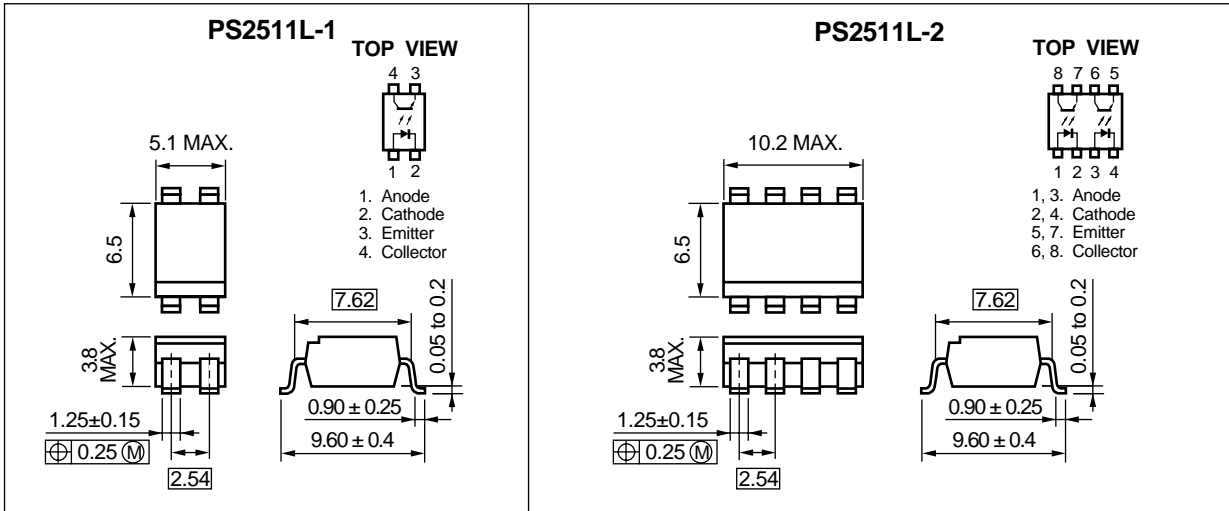
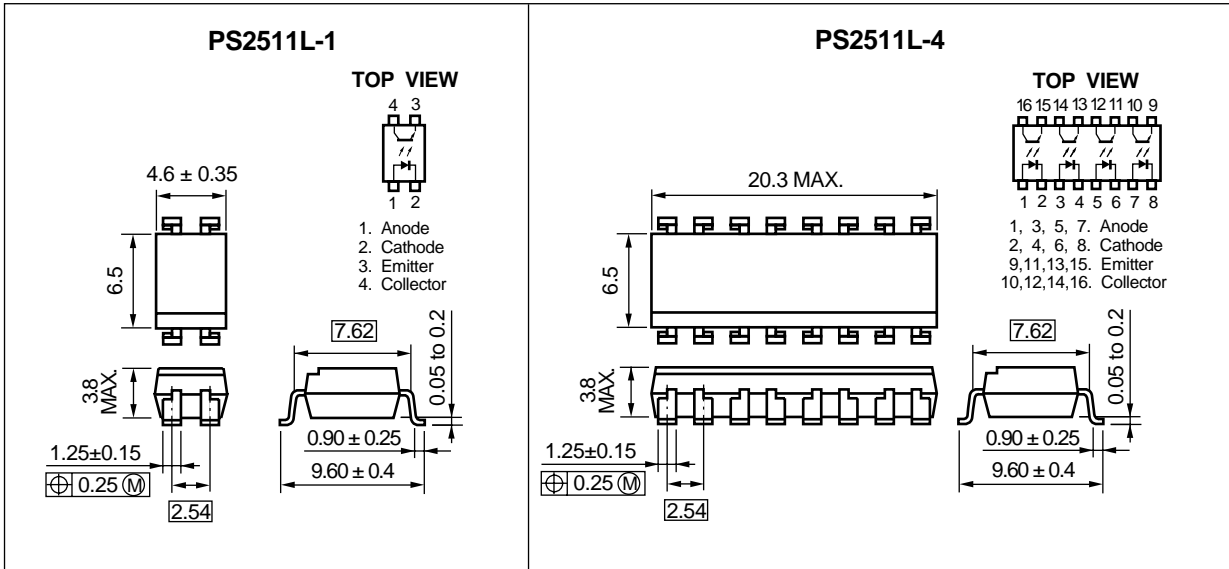
The information in this document is subject to change without notice.

PACKAGE DIMENSIONS (in millimeters)

DIP (Dual In-line Package)



Lead Bending Type (Gull-wing)



ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C, unless otherwise specified)

Parameter		Symbol	Ratings		Unit
			PS2511-1, PS2511L-1	PS2511-2,-4 PS2511L-2,-4	
Diode	Reverse Voltage	V _R	6		V
	Forward Current (DC)	I _F	50		mA
	Power Dissipation Derating	ΔP _D /°C	0.7	0.55	mW/°C
	Power Dissipation	P _D	70	55	mW/ch
	Peak Forward Current ^{*1}	I _{FP}	1		A
Transistor	Collector to Emitter Voltage	V _{CEO}	40		V
	Emitter to Collector Voltage	V _{Eco}	5		V
	Collector Current	I _C	40		mA
	Power Dissipation Derating	ΔP _C /°C	1.5	1.2	mW/°C
	Power Dissipation	P _C	150	120	mW/ch
Isolation Voltage ^{*2}		BV	5 000		Vr.m.s.
Operating Ambient Temperature		T _A	-55 to +100		°C
Storage Temperature		T _{stg}	-55 to +150		°C

*1 PW = 100 μs, Duty Cycle = 1 %

*2 AC voltage for 1 minute at T_A = 25 °C, RH = 60 % between input and output

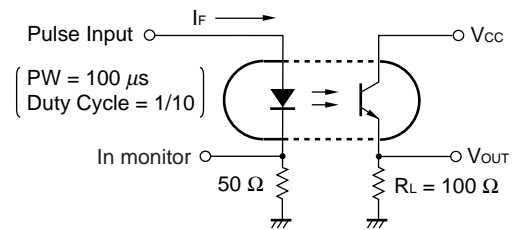
ELECTRICAL CHARACTERISTICS (T_A = 25 °C)

Parameter		Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Diode	Forward Voltage	V _F	I _F = 10 mA		1.2	1.4	V
	Reverse Current	I _R	V _R = 5 V			5	μA
	Terminal Capacitance	C _t	V = 0 V, f = 1.0 MHz		50		pF
Transistor	Collector to Emitter Dark Current	I _{CEO}	V _{CE} = 40 V, I _F = 0 mA			100	nA
Coupled	Current Transfer Ratio (I _c /I _F) ^{*1}	CTR	I _F = 5 mA, V _{CE} = 5 V	80	200	400	%
	Collector Saturation Voltage	V _{CE(sat)}	I _F = 10 mA, I _c = 2 mA			0.3	V
	Isolation Resistance	R _{I-O}	V _{I-O} = 1.0 kV _{DC}	10 ¹¹			Ω
	Isolation Capacitance	C _{I-O}	V = 0 V, f = 1.0 MHz		0.5		pF
	Rise Time ^{*2}	t _r	V _{CC} = 10 V, I _c = 2 mA, R _L = 100 Ω		3		μs
	Fall Time ^{*2}	t _f			5		

*1 CTR rank (PS2511-1,PS2511L-1 only)

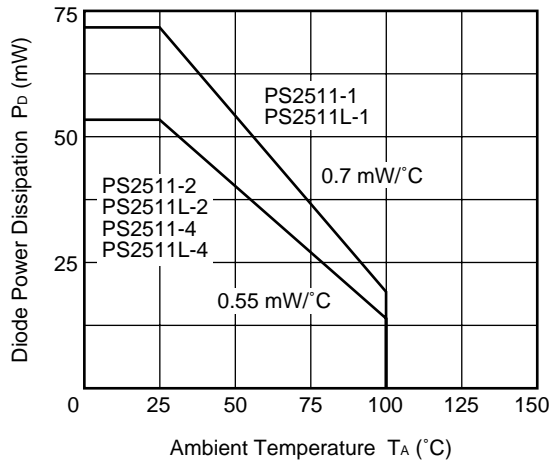
D : 100 to 300 %

*2 Test Circuit for Switching Time

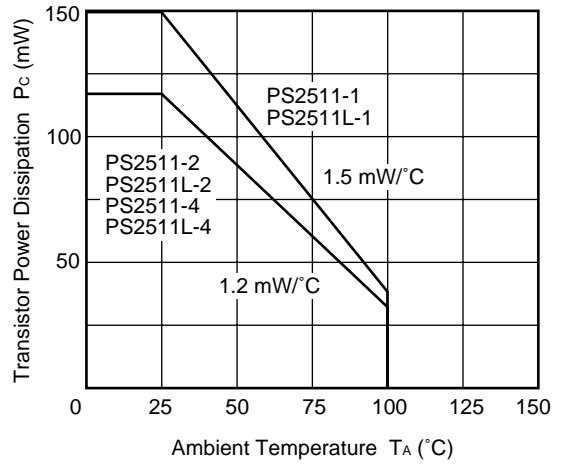


TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise specified)

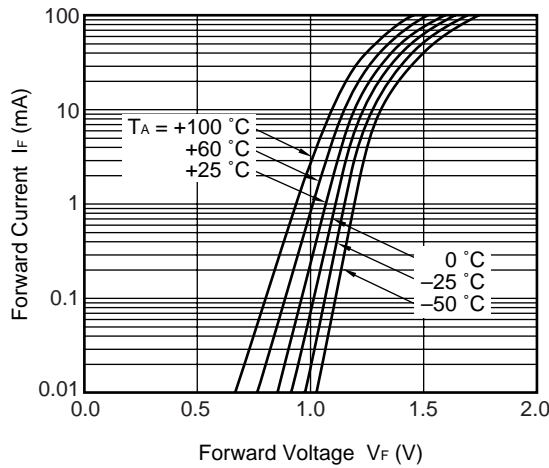
DIODE POWER DISSIPATION vs. AMBIENT TEMPERATURE



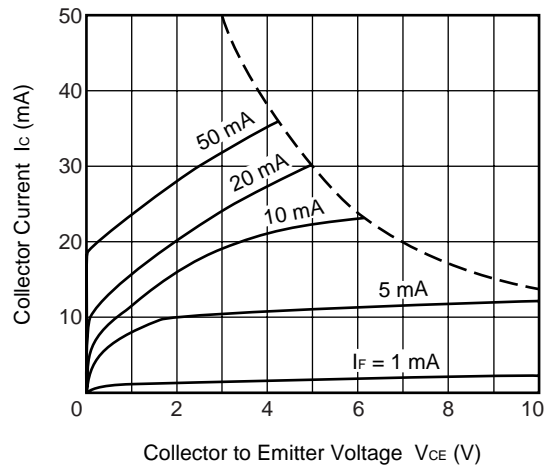
TRANSISTOR POWER DISSIPATION vs. AMBIENT TEMPERATURE



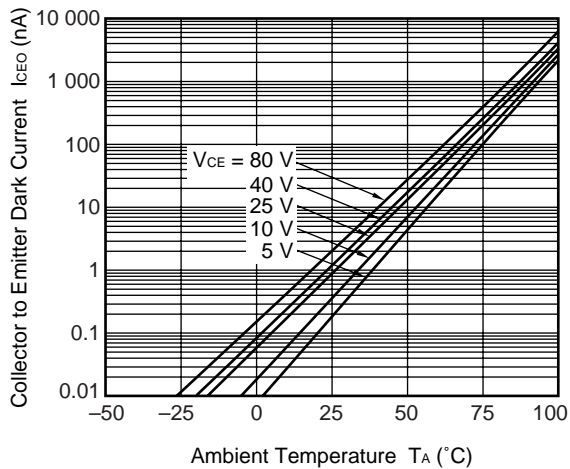
FORWARD CURRENT vs. FORWARD VOLTAGE



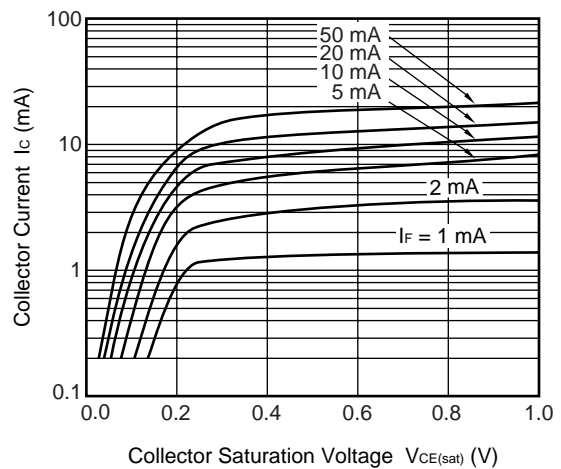
COLLECTOR CURRENT vs. COLLECTOR TO EMITTER VOLTAGE



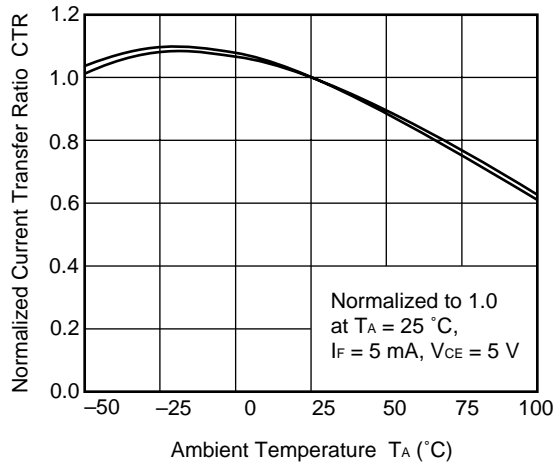
COLLECTOR TO EMITTER DARK CURRENT vs. AMBIENT TEMPERATURE



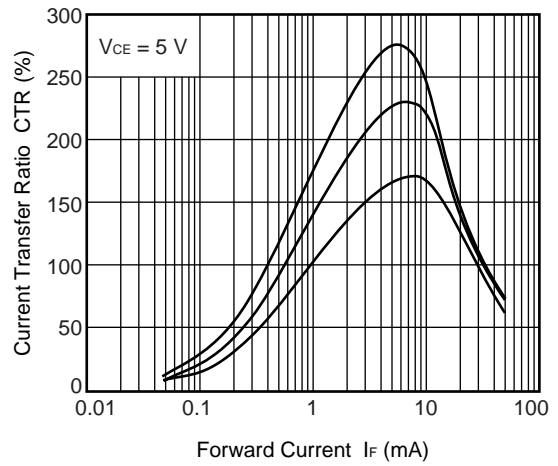
COLLECTOR CURRENT vs. COLLECTOR SATURATION VOLTAGE



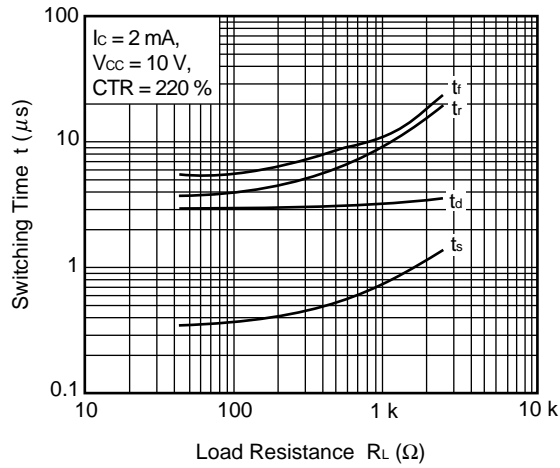
NORMALIZED CURRENT TRANSFER RATIO vs. AMBIENT TEMPERATURE



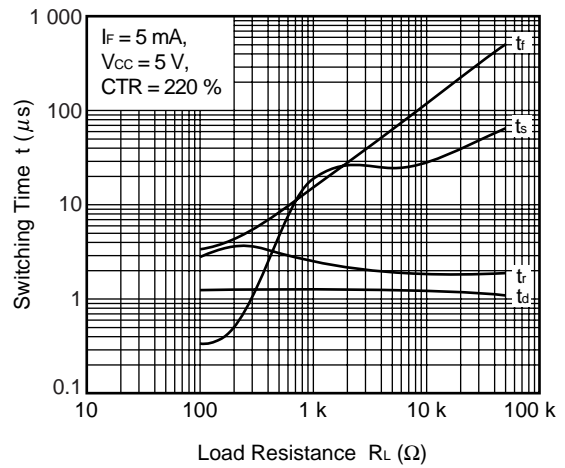
CURRENT TRANSFER RATIO vs. FORWARD CURRENT



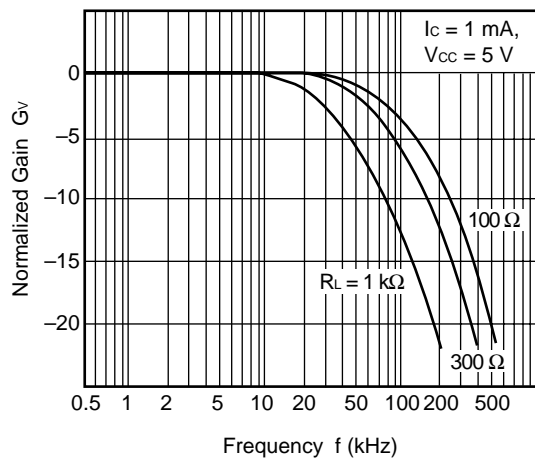
SWITCHING TIME vs. LOAD RESISTANCE



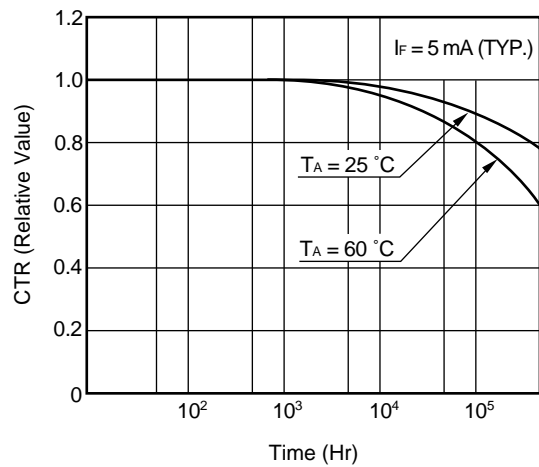
SWITCHING TIME vs. LOAD RESISTANCE



FREQUENCY RESPONSE



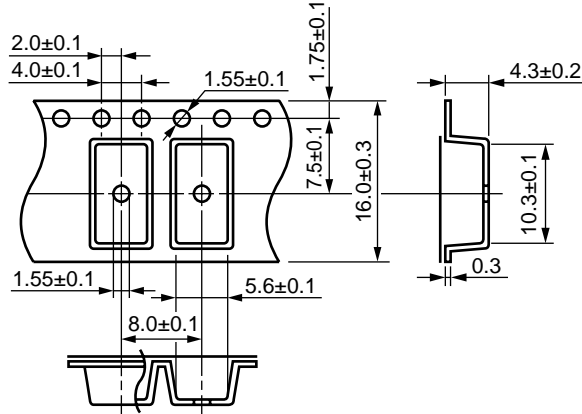
LONG TERM CTR DEGRADATION



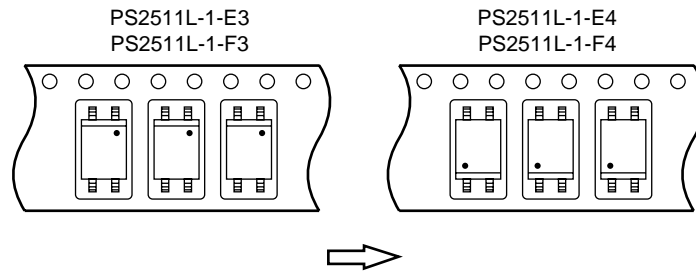
Remark The graphs indicate nominal characteristics.

TAPING SPECIFICATIONS (in millimeters)

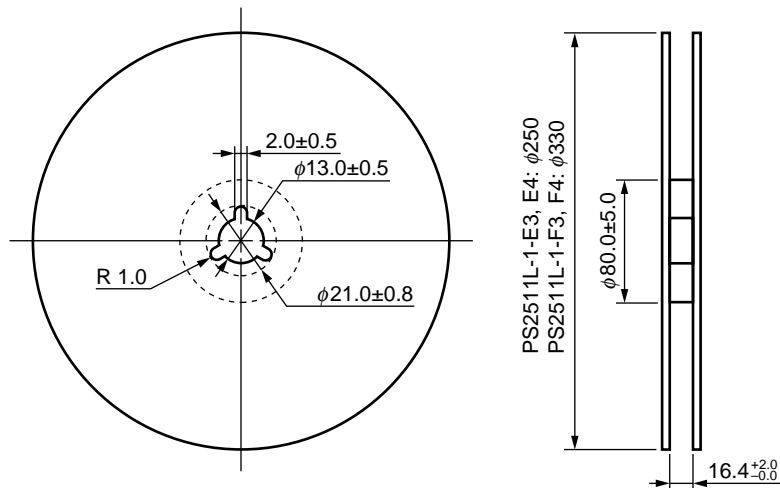
Outline and Dimensions (Tape)



Tape Direction

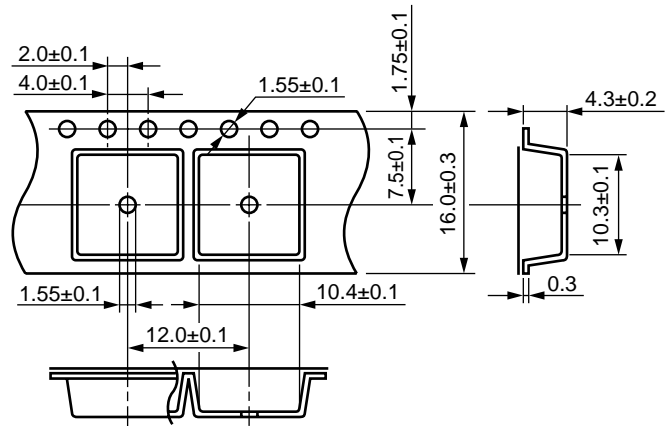


Outline and Dimensions (Reel)

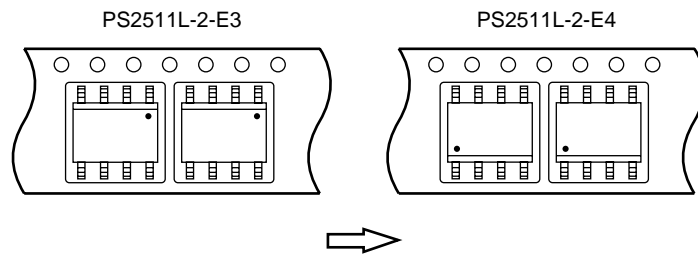


Packing: PS2511L-1-E3, E4 1 000 pcs/reel
 PS2511L-1-F3, F4 2 000 pcs/reel

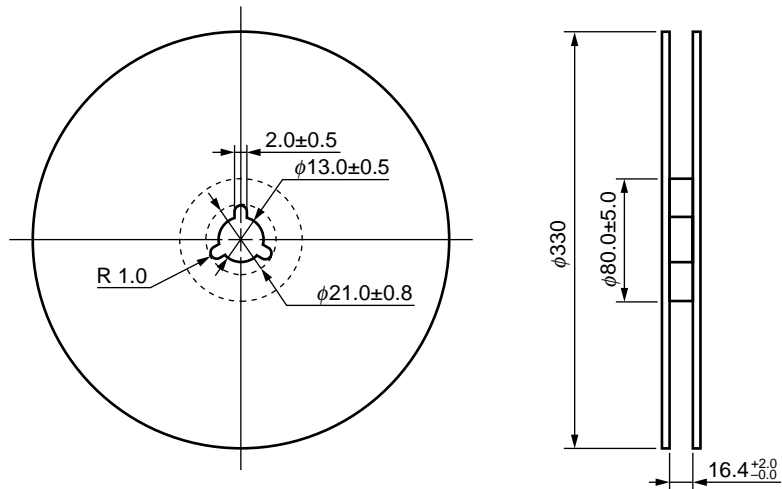
Outline and Dimensions (Tape)



Tape Direction



Outline and Dimensions (Reel)



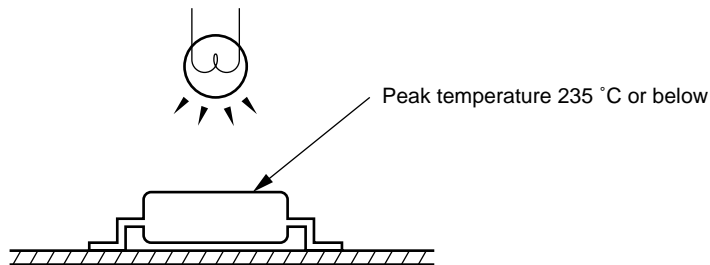
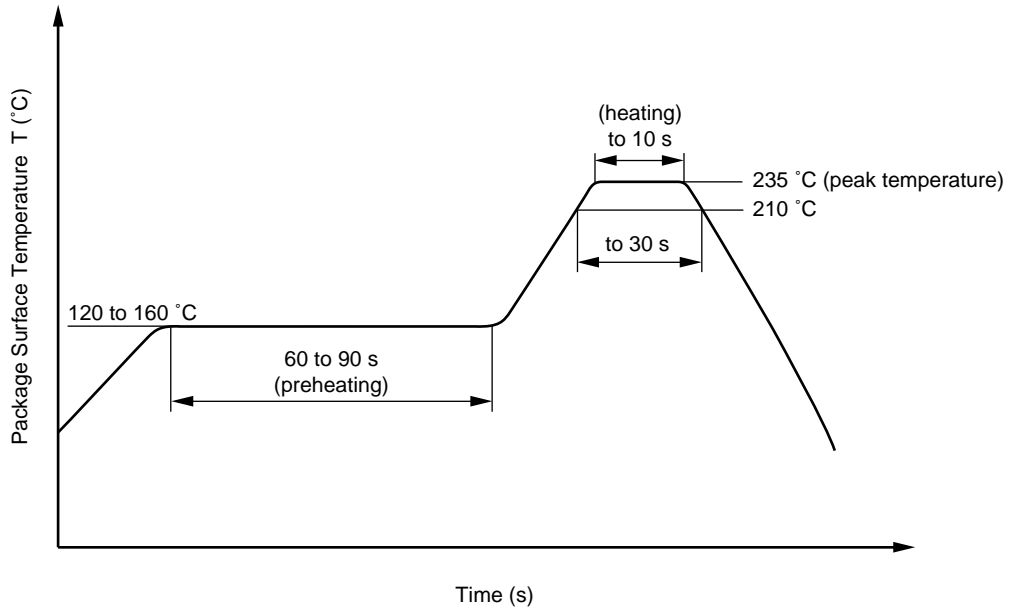
Packing: 1 000 pcs/reel

RECOMMENDED SOLDERING CONDITIONS

(1) Infrared reflow soldering

- Peak reflow temperature 235 °C (package surface temperature)
- Time of temperature higher than 210 °C 30 seconds or less
- Number of reflows Three
- Flux Rosin flux containing small amount of chlorine (The flux with a maximum chlorine content of 0.2 Wt % is recommended.)

Recommended Temperature Profile of Infrared Reflow



(2) Dip soldering

- Temperature 260 °C or below (molten solder temperature)
- Time 10 seconds or less
- Number of times One
- Flux Rosin flux containing small amount of chlorine (The flux with a maximum chlorine content of 0.2 Wt % is recommended.)

(3) Cautions

- Fluxes
Avoid removing the residual flux with freon-based and chlorine-based cleaning solvent.

[MEMO]

CAUTION

Within this device there exists GaAs (Gallium Arsenide) material which is a harmful substance if ingested. Please do not under any circumstances break the hermetic seal.

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Special: Transportation equipment (automobiles, trains, ships, etc.), traffic control systems, anti-disaster systems, anti-crime systems, safety equipment and medical equipment (not specifically designed for life support)

Specific: Aircrafts, aerospace equipment, submersible repeaters, nuclear reactor control systems, life support systems or medical equipment for life support, etc.

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Anti-radioactive design is not implemented in this product.